

- (2) (146) US-20030109093-A1.DID. (((((charge near3 strap\$4 trap\$4 nitride))))
- (2) (147) (((((charge near3 strap\$4 trap\$4 nitride))))
- (2) (148) (((charge near3 strap\$4 trap\$4 nitride))))
- (2) (4) "20030109093" 6,670,671 pn.
- (2) (4792184) conduct\$4 metal
- (2) (6730) ((insulat\$5 dielectric oxide)) near4 (oxidizing oxidized) with (conduct\$4 me
- (2) (145548) first adj2 (conduct\$4 metal)
- (2) (477) (first adj2 (conduct\$4 metal)) with ((insulat\$5 dielectric oxide))
- (2) (0) (first adj2 (conduct\$4 metal)) with ((insulat\$5 dielectric oxide))
- (2) (21) ((first adj2 (conduct\$4 metal)) with ((insulat\$5 dielectric oxide)))
- (2) (30) ((insulat\$5 dielectric oxide))
- (2) (5749) bird adj beat
- (2) (5748) bird\$2 adj beat
- (2) (110) (bird adj beat)) and ((sonos monos minos))))
- (2) (38) ((bird adj beat))
- (2) (18) ((insulat\$5 dielectric oxide))
- (2) (2) 6645801.pn.
- (2) (2) 6645801.pn. and ((wordline "WL" ((word digit control adj gate) adj line) word ne
- (2) (260209) \$7icid\$4 silicat\$4)
- (2) (2) 6645801.pn. and (\$7icid\$4 silicat\$4))
- (2) (2) 6524913.pn.
- (2) (3) diffusion near5 ion adj implantation
- (2) (5553) diffusion near5 ion adj implantation
- (2) (4059053) (source near drain source adj drain drain adj source s/d d/s active adj regi
- (2) (620) (diffusion near5 ion adj implantation) with ((source near drain source adj drain
- (2) (4024992) (source near drain source adj drain drain adj source s/d d/s))

		Browse	Queue	Clear	
	CBS	USPAT-US-POPLIB-EPO-JPO-DERWENT-IBM-TDG			Plurals
	Default operator:	OR			<input checked="" type="checkbox"/> Highlight all the terms initially
(((((charge near3 strap\$4 trap\$4 nitride))))					
) same ((bl billing bit adj line readline read adj line sense adj line) same ((wordline "WL" ((word digit control adj gate) adj line) word near (read\$3 wrt\$3)))					
)) and ((sonos monos minos))					
)) no1 (((((charge near3 strap\$4 trap\$4 nitride))))					
) same ((bl billing bit adj line readline read adj line sense adj line) same ((wordline "WL" ((word digit control adj gate) adj line) word near (read\$3 wrt\$3)))					
)) and ((sonos monos minos))					
)) and ((insulat\$5 dielectric oxide))					
) near4 (oxidizing oxidized)) ((4173766" "5168334" "5284784" "5349221" "5717835" "5768192" "5988603" "5972751" "8001689" "8023085" "8030871" "8074915" "8130453" "8143608" "8153467" "8153471" "8157575" "8159795")PN.)6645801.URPN. ("5349221" "5907171" "8408980")PN.)6541818.URPN. ("8458881" "6465303" "2002/0086548")PN.)6524913.URPN. ("4173766" "5168334" "5349221" "5644533" "5768192" "5825686" "5963465" "5966603" "6001709" "6011725" "6030871" "6117730" "6287817" "6326268")PN.)6488865.URPN.)20030109093" 6,670,671.pn.)					

A B C D E F G H I J K L M N O P Q R S T U V W X Y Z

#	Inventor	Document Issue	Title	Current Status	Current XML	Reviewed	S	C	P	Search	Desc	P
1	<input type="checkbox"/>	Harari, Eliyah	US 200301020030.3	Multi-state non-volatile integrated circuit me	438/200-257/E21.68	R	I	F	R	<input type="checkbox"/>	US 200301	
2	<input type="checkbox"/>	Chen, Chien-	US 6784483 200401	Method for preventing hole and electron mov	257/317-257/315	R	I	F	R	<input type="checkbox"/>	US 678448	
3	<input type="checkbox"/>	Sasago, Yosh	US 6870871 20031.3	Nonvolatile semiconductor memory device a	257/319-257/345	R	C	C	R	<input type="checkbox"/>	US 687087	
4	<input checked="" type="checkbox"/>	Hamsbey, Ma	US 6645801 20031.1	Salicidized gate for virtual ground arrays	438/216-257/314	R	I	F	R	<input type="checkbox"/>	US 664580	
5	<input type="checkbox"/>	Ramsbey, Ma	US 6541816 20030.2	Planar structure for non-volatile memory dev	257/324-257/E21.67	R	I	T	R	<input type="checkbox"/>	US 654181	
6	<input type="checkbox"/>	Lin, Hung-Sui	US 6524913 20030.7	Method of fabricating a non-volatile memory	438/201-438/287	R	C	C	R	<input type="checkbox"/>	US 652491	
7	<input type="checkbox"/>	Eitan, Boaz	US 5866603 18991.9	NROM fabrication method with a periphery p	438/258-257/E21.67	R	I	F	R	<input type="checkbox"/>	US 586660	
8	<input type="checkbox"/>	Eitan, Boaz	US 5768192 19980.1	Non-volatile semiconductor memory cell utili	365/185-257/E29.30	R	I	F	R	<input type="checkbox"/>	US 576819	
9	<input type="checkbox"/>	Lee, Thomas	US 2004020 20041.1	Dense arrays and charge storage devices	257/296	R	I	F	R	<input type="checkbox"/>	US 200402	
10	<input type="checkbox"/>	Vyvoda, Mich	US 2004018 20040.8	Multiple-mode memory and method for formi	365/51	R	C	C	R	<input type="checkbox"/>	US 200401	

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